## Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch

### **ABSOLUTE MAXIMUM RATINGS**

(All voltages referenced to GND.)
V <sub>DD</sub> Logic Supply Voltage Range0.3V to +5.6V
V <sub>CC</sub> Positive Driver Supply Voltage Range0.3V to +5.6V
V <sub>EE</sub> Negative Driver Supply Voltage Range5.6V to +0.3V
V <sub>NNA</sub> , V <sub>NNB</sub> High Negative
Supply Voltage Range110V to +0.3V
V <sub>PPA</sub> , V <sub>PPB</sub> High Positive
Supply Voltage Range0.3V to +110V
OUT_Output Voltage RangeV <sub>NN</sub> to V <sub>PP</sub>
LVOUT_ Output Voltage Range
(100mA Maximum Current)1.2V to +1.2V
DINN_, DINP_, CC_, SYNC, LDO_EN0.3V to +5.6V
CLK, CLK, MODE_ Voltage Range0.3V to (V <sub>CC</sub> + 0.3V)

THP Logic Output Voltage Range0.3V to +5.6V
V <sub>GPA</sub> , V <sub>GPB</sub> Output Voltage Rangemax[(V <sub>PP</sub> - 5.6V), (V <sub>FE</sub> + 0.6V)] to (V <sub>PP</sub> + 0.3V)
V <sub>GNA</sub> , V <sub>GNB</sub> Output Voltage
Range(V <sub>NN</sub> - 0.3V) to min[(V <sub>CC</sub> + 0.6V), (V <sub>NN</sub> + 5.6V)]
Continuous Power Dissipation ( $T_A = +70^{\circ}C$ )
TQFN (derate 50mW/°C above +70°C)4000mW
Operating Temperature Range40°C to +85°C
Maximum Junction Temperature+150°C
Storage Temperature Range65°C to +150°C
Lead Temperature (soldering, 10s)+300°C
Soldering Temperature (reflow)+260°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### PACKAGE THERMAL CHARACTERISTICS (Note 1)

TQFN

 $\label{eq:constraint} Junction-to-Ambient Thermal Resistance (\theta_{JA})...........20°C/W \qquad Junction-to-Case Thermal Resistance (\theta_{JC})...........0.5°C/W$ 

Note 1: Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to <a href="https://www.maximintegrated.com/thermal-tutorial">www.maximintegrated.com/thermal-tutorial</a>.

### DC ELECTRICAL CHARACTERISTICS

 $(V_{DD} = +3V, V_{CC} = +5V, V_{EE} = -5V, V_{PPA} = +100V, V_{NNA} = -100V, V_{PPB} = +100V, V_{NNB} = -100V, 1\mu$ F bypass capacitor between V<sub>GNA</sub> and V<sub>NNA</sub>, 1µF bypass capacitor between V<sub>GPA</sub> and V<sub>PPA</sub>, 1µF bypass capacitor between V<sub>GPA</sub> and V<sub>PPA</sub> and

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS
POWER SUPPLIES (V <sub>DD</sub> , V <sub>CC</sub> , V	/ <sub>EE</sub> , V <sub>PP_</sub> , V <sub>M</sub>	NN_)				
Logic Supply Voltage	V <sub>DD</sub>		+1.7	+3	+5.25	V
Positive Drive Supply Voltage	V <sub>CC</sub>		+4.9	+5	+5.1	V
Negative Drive Supply Voltage	V <sub>EE</sub>		-5.1	-5	-4.9	V
High-Side Supply Voltage	V <sub>PP</sub> _		0		+105	V
Low-Side Supply Voltage	V <sub>NN</sub> _		-105		0	V
External Low-Side LDO Voltage	V <sub>GN</sub> V <sub>NN</sub> _	LDO_EN = high	5	5.3	5.5	V
External High-Side LDO Voltage	V <sub>PP</sub> V <sub>GP</sub> _	LDO_EN = high	5	5.3	5.5	V
External Floating Power-Supply Current from V <sub>GN</sub> _	I <sub>VGN_</sub>	LDO_EN = high (Note 3)	50			mA
External Floating Power-Supply Current from V <sub>GP</sub>	I <sub>VGP</sub> _	LDO_EN = high (Note 3)	85			mA
LOGIC INPUTS/OUTPUTS (DINN	I_, DINP_, MO	DDE_, SYNC, CC_, LDO_EN)				
Low-Level Input Threshold	VIL			0	.2 x V <sub>DD</sub>	V
High-Level Input Threshold	V <sub>IH</sub>		0.8 x V <sub>C</sub>	D		V
Logic Input Capacitance	C <sub>IN</sub>			4		pF

# Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch

## DC ELECTRICAL CHARACTERISTICS (continued)

 $(V_{DD} = +3V, V_{CC} = +5V, V_{EE} = -5V, V_{PPA} = +100V, V_{NNA} = -100V, V_{PPB} = +100V, V_{NNB} = -100V, 1\mu F bypass capacitor between V_{GNA} and V_{NNA}$ , 1µF bypass capacitor between V\_{GNB} and V\_{NNB}, 1µF bypass capacitor between V\_{GPA} and V\_{PPA}, 1µF bypass capacitor between V\_{GPB} and V\_{PPB}, V\_{LDO} = 0V, no load, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.) (Note 2)

PARAMETER	SYMBOL	CO	NDITIONS	MIN	ТҮР	MAX	UNITS
Logic Input Leakage (All Inputs Except LDO_EN)	I <sub>IN</sub>	$V_{IN} = 0V \text{ or } V_{DD}$		-1	0	+1	μA
LDO_EN Pulldown Resistance	R <sub>LDO_EN</sub>			7	10	14	kΩ
THP Low-Level Output Voltage	V <sub>OL</sub>	Pullup resistor to \	$I_{\rm DD} (R_{\rm PULLUP} = 1 k\Omega)$		0	.1 x V <sub>DD</sub>	V
CLOCK INPUTS (CLK, CLK)-D	IFFERENTIA	LMODE					
Differential Clock Input Voltage Range	V <sub>CLKD</sub>			0.2		2	V <sub>P-P</sub>
Common-Mode Voltage	V <sub>CLKCM</sub>				V <sub>CC</sub> /2		V
Common-Mode Voltage Range	V <sub>CL</sub>			V <sub>CC</sub> /2 - 0.45		V <sub>CC</sub> /2 + 0.45	V
Input Desistance	R <sub>CLK</sub> ,	Differential			7		kΩ
Input Resistance	RCLK	Common mode			23		kΩ
Input Capacitance	C <sub>CLK</sub> , C <u>CLK</u>	Capacitance to GND (each input)			4		pF
CLOCK INPUTS (CLK, CLK)-S	INGLE-ENDE	D MODE (V <sub>CLK</sub> < 0	0.1V)				
Low-Level Input	V <sub>IL</sub>	CLK			0	.2 x V <sub>DD</sub>	V
High-Level Input	VIH	CLK		0.8 x V <sub>C</sub>	D		V
Single-Ended Mode Selection Threshold Low	V <sub>IL</sub>	CLK				0.1	V
Single-Ended Mode Selection Threshold High	V <sub>IH</sub>	CLK		1			V
Input Capacitance (CLK)	C <sub>CLK</sub>				4		pF
Logic Input Leakage (CLK)	ICLK	$V_{CLK} = 0V \text{ or } V_{DD}$	)	-1	0	+1	μΑ
Pullup Current (CLK)	ICLK	$V_{\overline{CLK}} = 0V$			120	180	μA
SUPPLY CURRENT—SHUTDOV	VN MODE (M	ODE0 = Low, MOD	E1 = Low)				
V <sub>DD</sub> Supply Current	I <sub>DD</sub>	All inputs connect	ed to GND or V <sub>DD</sub>			3	μΑ
V <sub>CC</sub> Supply Current	I <sub>CC</sub>	All inputs connect	ed to GND or V <sub>DD</sub>			22	μΑ
V <sub>EE</sub> Supply Current	I <sub>EE</sub>	All inputs connect	ed to GND or V <sub>DD</sub>			13	μΑ
V <sub>PP</sub> _Supply Current	I <sub>PP</sub> _	All inputs connect	ed to GND or V <sub>DD</sub>			10	μΑ
V <sub>NN</sub> _Supply Current	I <sub>NN_</sub>	All inputs connect	ed to GND or V <sub>DD</sub>			10	μΑ
SUPPLY CURRENT—DISABLE	MODE (MOD	E0 = High, MODE1	= High)	·			
		All inputs	Transparent or single- ended clock mode		1.7	3	
V <sub>DD</sub> Supply Current	IDDQ	connected to GND or V <sub>DD</sub>	Differential clock mode, V <sub>CLKD</sub> = 0.2V		110	190	μA

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## DC ELECTRICAL CHARACTERISTICS (continued)

 $((V_{DD} = +3V, V_{CC} = +5V, V_{EE} = -5V, V_{PPA} = +100V, V_{NNA} = -100V, V_{PPB} = +100V, V_{NNB} = -100V, 1\mu$ F bypass capacitor between V<sub>GNA</sub> and V<sub>NNA</sub>, 1µF bypass capacitor between V<sub>GPA</sub> and V<sub>PPA</sub>, 1µF bypass capacitor between V<sub>GPA</sub> and V<sub>PPA</sub>, 1µF bypass capacitor between V<sub>GPB</sub> and V<sub>PPB</sub>,  $V_{LDO} = 0V$ , no load, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS		MIN	ТҮР	MAX	UNITS	
		DINN_ = DINP_ = GN	D		0.26	0.4		
V <sub>EE</sub> Supply Current	I <sub>EEQ</sub>	DINN_ = DINP_ =	MAX14808		9.4	13	mA	
		V <sub>DD</sub>	MAX14809		1.37	2		
		DINN_ = DINP_ = GN	D		0.49	0.75		
V <sub>CC</sub> Supply Current	ICCQ	DINN_ = DINP_ =	MAX14808		9.6	13.2	mA	
		V <sub>DD</sub>	MAX14809		1.6	2.3		
V <sub>CC</sub> Supply Current Increase in Clocked Mode	$\Delta I_{CC}$	Differential clock mod	е		3.5	5	mA	
V <sub>NN</sub> _Total Supply Current (Quiescent Mode)	I <sub>NNQ_</sub>	All inputs connected t	All inputs connected to GND or $V_{DD}$		195	305	μA	
V <sub>PP</sub> _Total Supply Current (Quiescent Mode)	I <sub>PPQ</sub> _	All inputs connected	All inputs connected to GND or $V_{DD}$		220	340	μA	
Total Power Dissipation per	P <sub>PDIS1</sub>	T/R switch off, damp ( mode)	off (transparent		5.7			
Channel (Disable Mode)		DINN_ = DINP_ =	MAX14808		17	mv	mW	
	P <sub>PDIS2</sub>	V <sub>DD</sub>	MAX14809		7			
SUPPLY CURRENT-OCTAL TH	REE-LEVEL	MODE, NO LOAD (MO	DE0 = High, MODE1	= Low)				
V <sub>DD</sub> Supply Current (Quiescent		All inputs connected	Transparent or single-ended clock mode		1.7	3		
Mode)		to GND or V <sub>DD</sub>	Differential clock mode, V <sub>CLKD</sub> = 0.2V		110	190	μΑ	
		DINN_ = DINP_ = GN	D		0.26	0.4		
V <sub>EE</sub> Supply Current (Quiescent	I <sub>EEQ</sub>	DINN_ = DINP_ =	MAX14808		9.4	13	mA	
Mode)		V <sub>DD</sub>	MAX14809		1.37	2	1	
		DINN_ = DINP_ = GN	D		0.49	0.75		
V <sub>CC</sub> Supply Current (Quiescent	ICCQ	 DINN_ = DINP_ =	MAX14808		9.6	13.2	mA	
Mode)		V <sub>DD</sub>	MAX14809		1.6	2.3	1	
V <sub>CC</sub> Supply Current Increase in Clocked Mode	ΔI <sub>CC</sub>	Differential clock mod	e		3.5	5	mA	
V <sub>NN</sub> _Total Supply Current (Quiescent Mode)	I <sub>NNQ_</sub>	All inputs connected t	o GND or V <sub>DD</sub>		195	305	μA	
V <sub>PP</sub> _Total Supply Current (Quiescent Mode)	I <sub>PPQ</sub>	All inputs connected t	o GND or V <sub>DD</sub>		220	340	μΑ	

# Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch

## DC ELECTRICAL CHARACTERISTICS (continued)

 $(V_{DD} = +3V, V_{CC} = +5V, V_{EE} = -5V, V_{PPA} = +100V, V_{NNA} = -100V, V_{PPB} = +100V, V_{NNB} = -100V, 1\mu$ F bypass capacitor between V<sub>GNA</sub> and V<sub>NNA</sub>, 1µF bypass capacitor between V<sub>GPA</sub> and V<sub>PPA</sub>, 1µF bypass capacitor between V<sub>GPA</sub> and V<sub>PPA</sub>, 1µF bypass capacitor between V<sub>GPB</sub> and V<sub>PPB</sub>,  $V_{LDO} = 0V$ , no load, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.) (Note 2)

PARAMETER	SYMBOL	CONDI	TIONS	MIN	TYP	MAX	UNITS
	P <sub>PDIS1</sub>	T/R switch off, damp mode)	off (transparent		5.7		
Total Power Dissipation per Channel (Quiescent Mode)		DINN_ = DINP_ =	MAX14808		17		mW
	P <sub>PDIS2</sub>	V <sub>DD</sub> (transparent mode)	MAX14809		7		
	I <sub>DD1</sub>	CW Doppler (Note 4) single-ended clock m	-		2.2	3.2	mA
V <sub>DD</sub> Supply Current		B mode (Note 5), tran single-ended clock m (MAX14808)			3.3	6	
	I <sub>DD2</sub>	B mode (Note 5), tran single-ended clock m (MAX14809)			10	20	μA
V <sub>EE</sub> Supply Current	I <sub>EE1</sub>	8 channels switching, CW Doppler (Note 4)	CC0 = high, CC1 = high		67	92	
	I <sub>EE2</sub> (Note 5) (Figure 1a),	MAX14808		9.7	14.8	mA	
		CC0 = low,	MAX14809		2	3	
	I <sub>CC1</sub>	8 channels switching, CW Doppler (Note 4)	CC0 = high, CC1 = high		45	60	
V <sub>CC</sub> Supply Current		8 channels switching, B mode	MAX14808		10	15	mA
	ICC2	(Note 5) (Figure 1a), CC0 = low, CC1 = low	MAX14809		2.1	3.2	
V <sub>DD</sub> Supply Current Increase in Clocked Mode	ΔI <sub>DD</sub>	Differential clock moc	le		1.8		mA
V <sub>CC</sub> Supply Current Increase in Clocked Mode	ΔI <sub>CC</sub>	Differential clock moc	le		3.8		mA
V Supply Current	I <sub>NN1</sub>	8 channels switching, high, CC1 = high, R <sub>L</sub> (Note 4)			157	200	
V <sub>NN</sub> _Supply Current	I <sub>NN2</sub>	8 channels switching, CC0 = low, CC1 = low 240pF (Note 5)			2	2.8	mA

# Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch

### DC ELECTRICAL CHARACTERISTICS (continued)

 $(V_{DD} = +3V, V_{CC} = +5V, V_{EE} = -5V, V_{PPA} = +100V, V_{NNA} = -100V, V_{PPB} = +100V, V_{NNB} = -100V, 1\mu F bypass capacitor between V_{GNA} and V_{NNA}$ , 1µF bypass capacitor between V\_{GNB} and V\_{NNB}, 1µF bypass capacitor between V\_{GPA} and V\_{PPA}, 1µF bypass capacitor between V\_{GPB} and V\_{PPB}, V\_{LDO} = 0V, no load, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.) (Note 2)

PARAMETER	SYMBOL	CONDI	TIONS	MIN	ТҮР	МАХ	UNITS
V <sub>PP</sub> Supply Current	I <sub>PP1</sub>	8 channels switching, high, CC1 = high, R <sub>L</sub> (Note 4)			186	230	mA
vpp_ Supply Cullent	$I_{PP2} \begin{array}{c} \text{8 channels switching, B mode (Figure 1a),} \\ \text{CC0 = low, CC1 = low, R_L = 1k}\Omega, C_L = \\ 240 \text{pF (Note 5)} \end{array}$			3.1	4.5		
	PD <sub>CW</sub>	1 channel switching,	CW Doppler (Note 4)		286		
Power Dissipation per Channel (Octal Three-Level Mode)	PD	1 channel switching, B mode (Note 5) (Figure 1a), CC0 =	MAX14808		73		mW
	R <sub>L</sub> =	$ \begin{array}{l} \text{IOW,} \\ \text{CC1} = \text{Iow,} \\ \text{R}_{\text{L}} = 1 \text{k} \Omega, \\ \text{C}_{\text{L}} = 240 \text{pF} \end{array} $	MAX14809		69.5		
SUPPLY CURRENT-QUAD FIVE	E-LEVEL DU	AL MODE, NO LOAD (	MODE0 = Low, MODE	E1 = High	ı)		
V <sub>DD</sub> Supply Current (Quiescent Mode)	Quiescent I <sub>DDQ</sub>	All inputs connected to GND or V <sub>DD</sub>	Transparent or single-ended clock mode		1.7	3	
			Differential clock mode, V <sub>CLKD</sub> = 0.2V		110	190	μΑ
		DINN_ = DINP_ = GN	D		0.26	0.4	
V <sub>EE</sub> Supply Current (Quiescent	I <sub>EEQ</sub>	DINN_ = DINP_ =	MAX14808		5.4	7.7	mA
Mode)		V <sub>DD</sub>	MAX14809		1.35	2	
		DINN_ = DINP_ = GND			0.49	0.75	
V <sub>CC</sub> Supply Current (Quiescent Mode)	ICCQ	DINN_ = DINP_ =	MAX14808		5.6	7.8	mA
Node)		V <sub>DD</sub>	MAX14809		1.6	2.3	
V <sub>CC</sub> Supply Current Increase	$\Delta I_{CC}$	Differential clock mod	e		3.5	5	mA
V <sub>NN</sub> _Supply Current (Quiescent Mode)	I <sub>NNQ_</sub>	All inputs connected t	to GND or V <sub>DD</sub>		195	305	μA
V <sub>PP</sub> _Supply Current (Quiescent Mode)	I <sub>PPQ</sub>	All inputs connected	to GND or V <sub>DD</sub>		220	340	μA
	P <sub>PDIS1</sub>	T/R switch off, DAMP mode)	off (transparent		11.3		
Power Dissipation per Channel (Quiescent Mode)	P <sub>PDIS2</sub> DINN_ =	DINN_ = DINP_ = V <sub>DD</sub> (transparent	MAX14808		24.1		mW
		mode)	MAX14809		14.1		

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### DC ELECTRICAL CHARACTERISTICS (continued)

 $(V_{DD} = +3V, V_{CC} = +5V, V_{EE} = -5V, V_{PPA} = +100V, V_{NNA} = -100V, V_{PPB} = +100V, V_{NNB} = -100V, 1\mu$ F bypass capacitor between V<sub>GNA</sub> and V<sub>NNA</sub>, 1µF bypass capacitor between V<sub>GPA</sub> and V<sub>PPA</sub>, 1µF bypass capacitor between V<sub>GPA</sub> and V<sub>PPA</sub> and

PARAMETER	SYMBOL	COND	TIONS	MIN	ТҮР	MAX	UNITS
	I <sub>DD1</sub>	4 channels switching (Note 4)	, CW Doppler		1.4		mA
V <sub>DD</sub> Supply Current	I <sub>DD2</sub>	4 channels switching, B mode (Note 5) (Figure 1a)			4.3		μA
	I <sub>EE1</sub>	4 channels switching, CW Doppler (Note 4)	CC0 = high, CC1 = high		33		
V <sub>EE</sub> Supply Current		Switching, Billoue	MAX14808		5.9		mA
	CC0 = low, CC1 = low	CC0 = low,	MAX14809		1.9		
V <sub>CC</sub> Supply Current	I <sub>CC1</sub>	4 channels switching, CW Doppler (Note 4)	CC0 = high, CC1 = high		22		
	4 channels switching, B mode I <sub>CC2</sub> (Note 5) (Figure 1a),	MAX14808		6		mA	
	ICC2	(Note 5) (Figure 1a), CC0 = low, CC1 = low	MAX14809		2		
V <sub>DD</sub> Supply Current Increase	$\Delta I_{DD}$	Differential clock mod	le		1.8		mA
V <sub>CC</sub> Supply Current Increase	$\Delta I_{CC}$	Differential clock mod	le		3.8		mA
V <sub>NN</sub> _Supply Current	I <sub>NN1</sub>	4 channels switching, CW Doppler (Note 4)	$\begin{array}{l} CC0 = high, \\ CC1 = high, \\ R_L = 1k\Omega, \\ C_L = 240 pF \end{array}$		90		mA
	I <sub>NN2</sub>	4 channels switching (Figure 1a), CC0 = lo		1.3			1
V <sub>PP</sub> _Supply Current	I <sub>PP1</sub>	4 channels switching, CW Doppler (Note 4)	$\begin{array}{l} CC0 = high, \\ CC1 = high, \\ R_L = 1k\Omega, \\ C_L = 240 pF \end{array}$		103		mA
	I <sub>PP2</sub>	4 channels switching (Figure 1a), CC0 = lo			2.2		

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### DC ELECTRICAL CHARACTERISTICS (continued)

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PARAMETER	SYMBOL	CONDI	TIONS	MIN	ТҮР	MAX	UNITS
	PD <sub>CW</sub>	1 channel switching, ( 4), $R_L = 1k\Omega$ , $C_L = 24$			311		
Total Power Dissipation per Channel (Quad Five-Level Dual Mode)	PD <sub>PW</sub>	1 channel switching, B mode (Note 5) (Figure 1a), CC0 = low,	MAX14808		102		mW
	· DPW	CC1 = low, $R_L = 1k\Omega,$ $C_L = 240pF$	MAX14809		94.5		
SUPPLY CURRENT—OCTAL TH +5V, V <sub>GN</sub> V <sub>NN</sub> _ = +5V)	REE-LEVEL	, NO LOAD (MODE0 =	High, MODE1 = Low	LDO_EN	Ī = High, '	V <sub>PP_</sub> - V <sub>C</sub>	6P_ =
V <sub>EE</sub> Supply Current (Quiescent Mode)	I <sub>EEQ_</sub>	All inputs connected	o GND		25	46	μA
V <sub>CC</sub> Supply Current (Quiescent Mode)	I <sub>CCQ</sub> _	All inputs connected	o GND		280	420	μA
V <sub>NN</sub> _Supply Current (Quiescent Mode)	I <sub>NNQ_</sub>	All inputs connected t	o GND		40	62	μA
V <sub>PP</sub> _Supply Current (Quiescent Mode)	I <sub>PPQ_</sub>	All inputs connected to GND			40	62	μA
OUTPUT STAGE							
			CC0 = low, CC1 = low		8.5		
V <sub>NNA.</sub> V <sub>NNB</sub> Connected Low-	Para	I <sub>OUT_</sub> = -50mA	CC0 = high, CC1 = low		10		Ω
Side Output Impedance	R <sub>OLS</sub>		CC0 = low, CC1 = high		13.5		
			CC0 = high, CC1 = high		26	48	
			CC0 = low, CC1 = low		9		
V <sub>PPA</sub> , V <sub>PPB</sub> Connected High-			CC0 = high, CC1 = low		10.5		Ω
Side Output Impedance	R <sub>OHS</sub>	I <sub>OUT</sub> _ = +50mA	CC0 = low, CC1 = high		14.5		
			CC0 = high, CC1 = high		27	53	
Clamp nFET Output Impedance	R <sub>ONG</sub>	I <sub>OUT</sub> _ = -50mA,			13.5		Ω
Clamp pFET Output Impedance	R <sub>OPG</sub>	$I_{OUT} = +50 \text{mA}$			13.5		Ω
Active Damp Output Impedance	R <sub>DAMP</sub>	Before grass-clipping	diode		500		Ω

# Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch

### DC ELECTRICAL CHARACTERISTICS (continued)

 $(V_{DD} = +3V, V_{CC} = +5V, V_{EE} = -5V, V_{PPA} = +100V, V_{NNA} = -100V, V_{PPB} = +100V, V_{NNB} = -100V, 1\mu F bypass capacitor between V_{GNA} and V_{NNA}$ , 1µF bypass capacitor between V\_{GNB} and V\_{NNB}, 1µF bypass capacitor between V\_{GPA} and V\_{PPA}, 1µF bypass capacitor between V\_{GPB} and V\_{PPB}, V\_{LDO} EN = 0V, no load, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.) (Note 2)

PARAMETER	SYMBOL	COND	ITIONS	MIN	ТҮР	МАХ	UNITS
			CC0 = low, CC1 = low		2.0		
V <sub>NNA,</sub> V <sub>NNB</sub> Connected Low-		V <sub>DS</sub> = +100V	CC0 = high, CC1 = low		1.5		
Side Output Current	IOLS	v <sub>DS</sub> = +100v	CC0 = low, CC1 = high		1.0		A
			CC0 = high, CC1 = high		0.5		
			CC0 = low, CC1 = low		2.0		
V <sub>PPA,</sub> V <sub>PPB</sub> Connected High- Side Output Current		V <sub>DS</sub> = +100V	CC0 = high, CC1 = low		1.5		A
	OHS	$V_{DS} = +100V$	CC0 = low, CC1 = high		1.0		A
			CC0 = high, CC1 = high		0.5		
GND-Connected nFET Output Current	I <sub>ONG</sub>	V <sub>DS</sub> = +100V			1		А
GND-Connected pFET Output Current	I <sub>OPG</sub>	$V_{DS} = +100V$			1		А
Diode Voltage Drop (Blocking Diode and Grass-Clipping Diode)	V <sub>DROP</sub>	$I_{OUT_} = \pm 50 mA$			1.7		V
LVOUT_Diode Clamping Voltage	LV <sub>CLAMP</sub>	I <sub>LOAD</sub> = 1mA (MAX1	4808 only)	-0.9		+1	V
Grass-Clipping Diode Reverse Capacitance	C <sub>REV</sub>				2.5		pF
OUT_ Equivalent Large-Signal Shunt Capacitance	C <sub>HS</sub>	200V <sub>P-P</sub> signal			80		pF
T/R Switch On Impedance	R <sub>ON</sub>	MAX14808 only			11.5		Ω
T/R Switch Off Impedance	R <sub>OFF</sub>	MAX14808 only		1			MΩ
LVOUT_ Output Offset	LV <sub>OFF</sub>	LVOUT_, OUT_ unconnected, $V_{CC} = +5V$ , $V_{EE} = -5V$		-40	0	+40	mV
THERMAL SHUTDOWN							
Thermal-Shutdown Threshold	t <sub>SDN</sub>	Temperature rising			+145		°C
Thermal-Shutdown Hysteresis	t <sub>HYS</sub>				20		°C

## Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch

### **AC ELECTRICAL CHARACTERISTICS**

 $(V_{DD} = +3V, V_{CC} = +5V, V_{EE} = -5V, V_{PPA} = +100V, V_{NNA} = -100V, V_{PPB} = +100V, V_{NNB} = -100V, V_{GNA}$  connected to  $V_{NNA}$  with 1µF capacitor, V<sub>GNB</sub> connected to V<sub>NNB</sub> with 1µF capacitor, V<sub>GPA</sub> connected to V<sub>PPA</sub> with 1µF capacitor, V<sub>GPB</sub> connected to V<sub>PPB</sub> with 1µF capacitor, V<sub>LDO\_EN</sub> = 0V, V<sub>CC0</sub> = 0V, V<sub>CC1</sub> = 0V, R<sub>L</sub> = 1k $\Omega$ , C<sub>L</sub> = 240pF, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.) (Note 2)

PARAMETER	SYMBOL	CON	DITIONS	MIN	ТҮР	MAX	UNITS
Logic Input to Output Rise Propagation Delay	t <sub>PLH</sub>	From 50% DINP_/DINN_ (transparent mode) to 10% OUT_ transition swing (Figure 2a)			18		ns
Logic Input to Output Fall Propagation Delay	t <sub>PHL</sub>	From 50% DINP_/DINN_ (transparent mode) to 10% OUT_ transition swing (Figure 2a)			18		ns
Logic Input to Output Rise to GND Propagation Delay	t <sub>PL0</sub>	From 50% DINP_/DINN_ (transparent mode) to 10% OUT_ transition swing (Figure 2a)			18		ns
Logic Input to Output Fall to GND Propagation Delay	t <sub>PH0</sub>	From 50% DINP_/DINN_ (transparent mode) to 10% OUT_ transition swing (Figure 2a)			18		ns
OUT_ Fall Time (V <sub>PPA</sub> to V <sub>NNA,</sub> V <sub>PPB</sub> to V <sub>NNB</sub> )	t <sub>FPN</sub>	Figure 2b			30	48	ns
OUT_ Rise Time (V <sub>NNA</sub> to V <sub>PPA</sub> , V <sub>NNB</sub> to V <sub>PPB</sub> )	t <sub>RNP</sub>	Figure 2b			30	48	ns
OUT_ Rise Time (GND to $V_{PPA}$ , GND to $V_{PPB}$ )	t <sub>ROP</sub>	Figure 2b			15	22.5	ns
OUT_ Fall Time (GND to $V_{\mbox{NNA},}$ GND to $V_{\mbox{NNB}}$	t <sub>FON</sub>	Figure 2b			15	22.5	ns
		20% to 80%	Three-level mode		21		
OUT_ Rise Time (V <sub>NNA</sub> to GND, V <sub>NNB</sub> to GND)	t <sub>RN0</sub>	transition (Figure 2b)	Five-level dual mode		13		ns
		20% to 80%	Three-level mode		21		
OUT_ Fall Time (V <sub>PPA</sub> to GND, V <sub>PPB</sub> to GND)	t <sub>FP0</sub>	transition (Figure 2b)	Five-level dual mode		13		ns
T/R Switch Turn-On Time	tontrsw	(MAX14808 only) Figure 3			0.65	1.2	μs
T/R Switch Turn-Off Time	t <sub>OFFTRSW</sub>	(MAX14808 only) Figure 3 (Note 6)			0.02	0.1	μs
Output Enable Time (Shutdown Mode to Normal Operation)	t <sub>EN1</sub>					100	μs
Output Disable Time (Normal Operation to Shutdown Mode)	t <sub>DIS1</sub>					10	μs

# Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch

### AC ELECTRICAL CHARACTERISTICS (continued)

 $(V_{DD} = +3V, V_{CC} = +5V, V_{EE} = -5V, V_{PPA} = +100V, V_{NNA} = -100V, V_{PPB} = +100V, V_{NNB} = -100V, V_{GNA}$  connected to  $V_{NNA}$  with 1µF capacitor,  $V_{GNB}$  connected to  $V_{NNB}$  with 1µF capacitor,  $V_{GPB}$  connected to  $V_{PPB}$  with 1µF capacitor,  $V_{LDO}$  = 0V,  $V_{CC0}$  = 0V,  $V_{CC1}$  = 0V,  $R_L$  = 1k $\Omega$ ,  $C_L$  = 240pF, unless otherwise noted. Typical values are at  $T_A$  = +25°C.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS
Output Enable Time (Transmit Disable Mode to Normal Operation)	t <sub>EN2</sub>				50	ns
Output Disable Time (Normal Operation to Transmit Disable Mode)	t <sub>DIS2</sub>				65	ns
Output Enable Time (Normal Operation to Sync Mode)	t <sub>EN3</sub>				4	μs
Output Disable Time (Sync Mode to Normal Operation)	t <sub>DIS3</sub>				500	ns
CLK Frequency	fCLK	$V_{DD} = 2.5V$			200	MHz
Input Setup Time (DINN_, DINP_)	t <sub>SETUP</sub>	$V_{DD} = 2.5V$	2			NS
Input Hold Time (DINN_, DINP_)	t <sub>HOLD</sub>	$V_{DD} = 2.5V$	0.5			ns
Second-Harmonic Distortion (Low Voltage)	THD2LV	f <sub>OUT</sub> = 5MHz, V <sub>PPA</sub> = -V <sub>NNA</sub> = +5V, V <sub>PPB</sub> = -V <sub>NNB</sub> = +5V, square wave (all modes)		-40		dBc
Second-Harmonic Distortion (High Voltage)	THD2HV	$f_{OUT}$ = 5MHz, V <sub>PPA</sub> = -V <sub>NNA</sub> = +100V, V <sub>PPB</sub> = -V <sub>NNB</sub> = +100V, square wave (all modes)		-43		dBc
Pulse Cancellation	PC1	$f_{OUT}$ = 5MHz, $V_{PPA}$ = $-V_{NNA}$ = +100V, $V_{PPB}$ = $-V_{NNB}$ = +100V, 2 periods, all harmonics of the summed signed with respect to the carrier		-40		dBc
	PC2	$f_{OUT}$ = 5MHz, $V_{PPA}$ = - $V_{NNA}$ = +100V, $V_{PPB}$ = - $V_{NNB}$ = +100V, 2 periods, $[(V_0 + V_{180})_{RMS}/(2 \times V_{0RMS})]_{dB}$		-40		
Pulser Bandwidth	BW	$V_{PP} = +60V, V_{NNA} = -60V (Figure 4)$		20		MHz
RMS Output Jitter	tj	$f_{OUT}$ = 5MHz, V <sub>PPA</sub> = -V <sub>NNA</sub> = +5V, V <sub>PPB</sub> = -V <sub>NNB</sub> = +5V, both in clocked mode or transparent mode (Figure 5)		6.25		ps

## **Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch**

### AC ELECTRICAL CHARACTERISTICS (continued)

 $(V_{DD} = +3V, V_{CC} = +5V, V_{EE} = -5V, V_{PPA} = +100V, V_{NNA} = -100V, V_{PPB} = +100V, V_{NNB} = -100V, V_{GNA} \text{ connected to } V_{NNA} \text{ with } V_{NNA} = -100V, V_{PPA} = -100V, V_$ 1µF capacitor, V<sub>GNB</sub> connected to V<sub>NNB</sub> with 1µF capacitor, V<sub>GPA</sub> connected to V<sub>PPA</sub> with 1µF capacitor, V<sub>GPB</sub> connected to V<sub>PPB</sub> with 1µF capacitor, V<sub>LDO EN</sub> = 0V, V<sub>CC0</sub> = 0V, V<sub>CC1</sub> = 0V, R<sub>L</sub> = 1kΩ, C<sub>L</sub> = 240pF, unless otherwise noted. Typical values are at  $T_A = +25^{\circ}C.$ ) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS
T/R Switch Harmonic Distortion (MAX14808)	THD <sub>TRSW</sub>	$R_{LOAD} = 200\Omega$ , $V_{SIGNAL} = 100mV_{P-P}$		-50		dB
T/R Switch Turn-On/Off Voltage Spike (MAX14808)	V <sub>SPIKE</sub>	$R_{LOAD}$ = 1k $\Omega$ at both sides of T/R switch		50		mV
Crosstalk	СТ	f = 5MHz, adjacent channels, $R_{LOUT_}$ = 200 $\Omega$		-51		dB

Note 2: All devices are 100% production tested at T<sub>A</sub> = +85°C. Limits over the operating temperature range are guaranteed by design. Note 3: Maximum operating current from V<sub>GN</sub> and V<sub>GP</sub> external power sources can vary depending on application requirements. The suggested minimum values assume 8 channels running in continuous transmission (CWD) at 5MHz with CC0 = CC1 = high.

**Note 4:** CW Doppler: continuous wave, f = 5MHz,  $V_{DD} = +3V$ ,  $V_{CC} = -V_{EE} = +5V$ ,  $V_{PP} = -V_{NN} = +5V$ . **Note 5:** B mode: f = 5MHz, PRF = 5kHz, 1 period,  $V_{DD} = +3V$ ,  $V_{CC} = -V_{EE} = +5V$ ,  $V_{PP} = -V_{NN} = +100V$ .

Note 6: T/R switch turn-off time is the time required to switch off the bias current of the T/R switch. The off-isolation is not guaranteed.

### Timing Diagrams

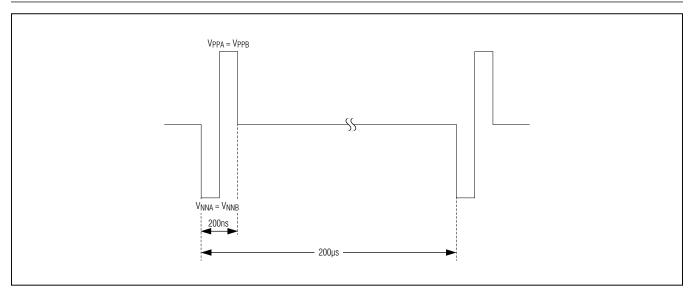


Figure 1a. High-Voltage Burst Test (Three Levels)

**Timing Diagrams (continued)** 

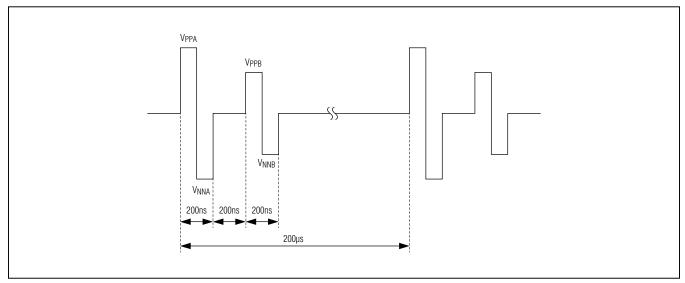


Figure 1b. High-Voltage Burst Test (Five Levels)

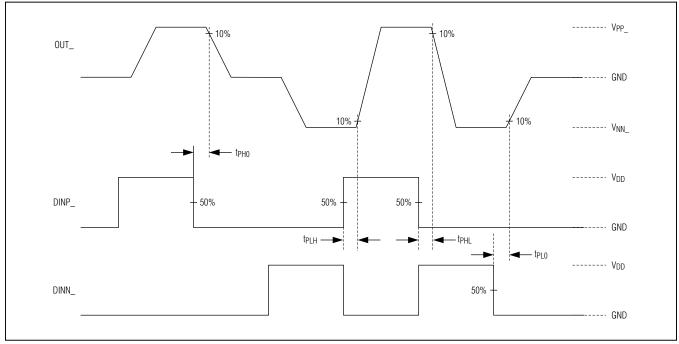


Figure 2a. Propagation Delay Timing

Timing Diagrams (continued)

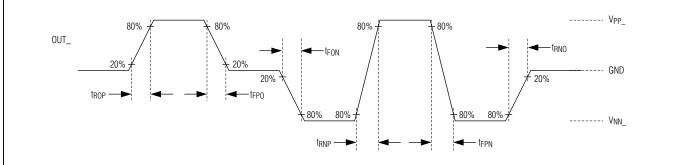


Figure 2b. Output Rise/Fall Timing

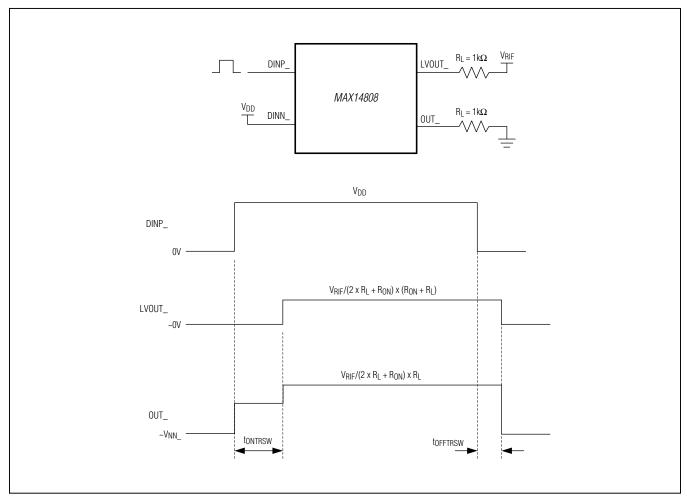


Figure 3. T/R Switch Turn-On/Off Time

**Timing Diagrams (continued)** 

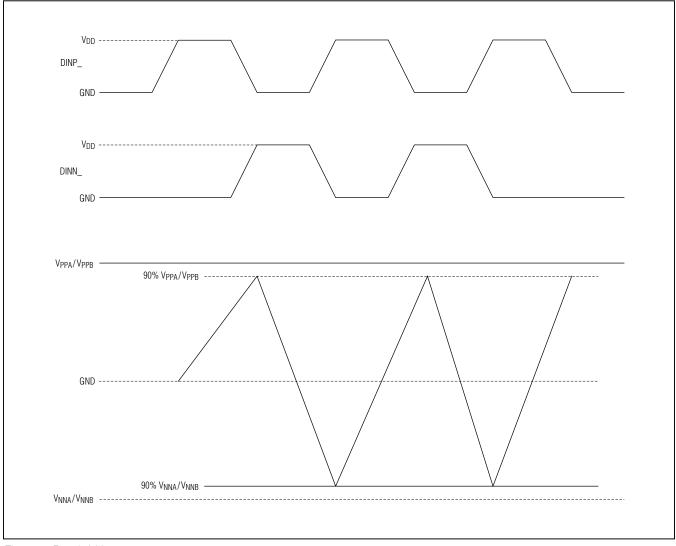


Figure 4. Bandwidth

**Timing Diagrams (continued)** 

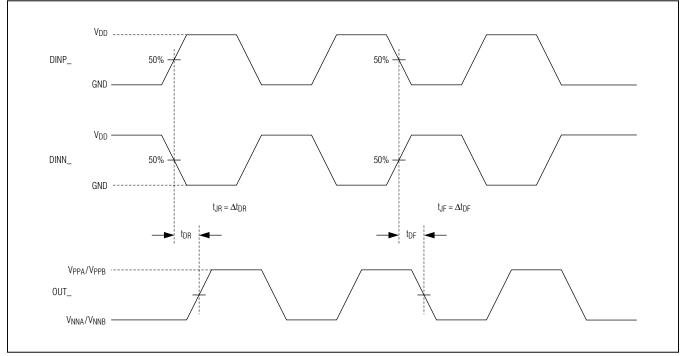
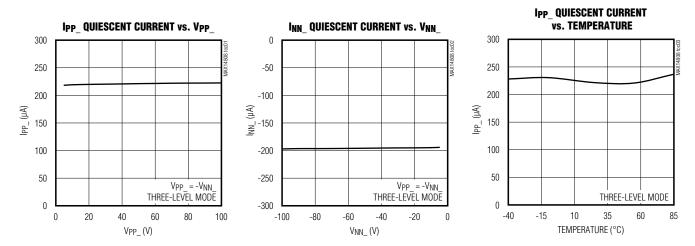


Figure 5. Jitter Timing

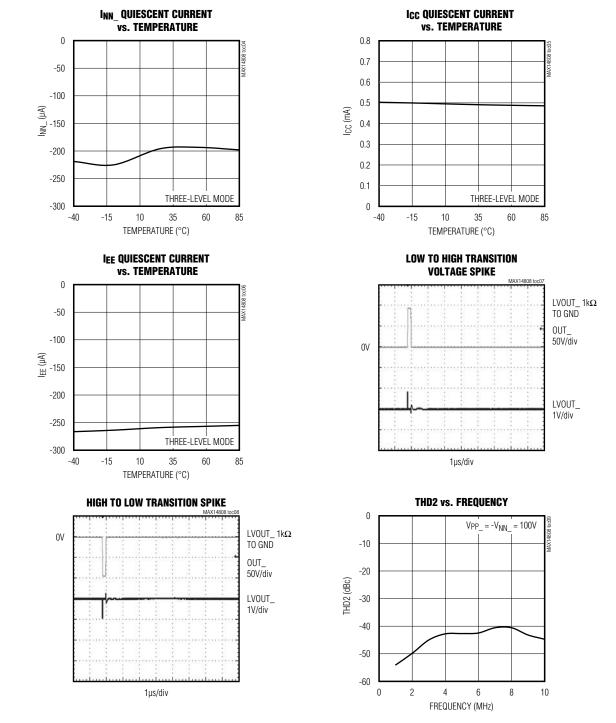
## **Typical Operating Characteristics**

 $(V_{DD} = +5V, V_{CC} = +5V, V_{EE} = -5V, V_{PP} = +100V, V_{NN} = -100V, R_L = 1k\Omega, C_L = 240pF$ , unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.)



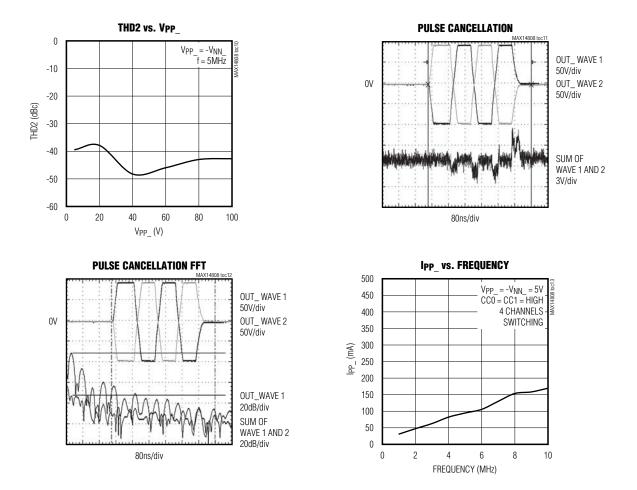
## **Typical Operating Characteristics (continued)**

(V<sub>DD</sub> = +5V, V<sub>CC</sub> = +5V, V<sub>EE</sub> = -5V, V<sub>PP</sub> = +100V, V<sub>NN</sub> = -100V, R<sub>L</sub> = 1kΩ, C<sub>L</sub> = 240pF, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.)



## **Typical Operating Characteristics (continued)**

 $(V_{DD} = +5V, V_{CC} = +5V, V_{EE} = -5V, V_{PP} = +100V, V_{NN} = -100V, R_L = 1k\Omega, C_L = 240pF$ , unless otherwise noted. Typical values are at  $T_A = +25^{\circ}C$ .)



## **Typical Operating Characteristics (continued)**

4 CHANNELS - ₩

SWITCHING

8

PROPAGATION

MAX14808 toc17

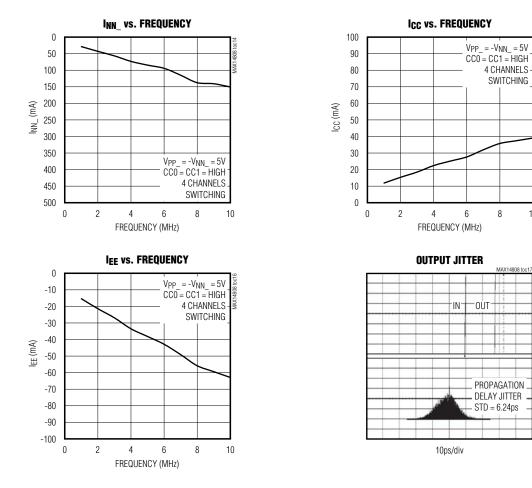
10

f = 5MHz

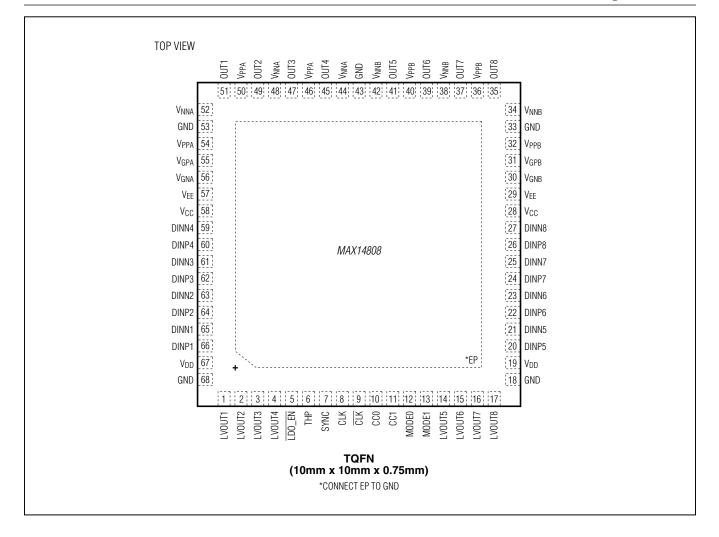
 $V_{PP} = 5V$ 

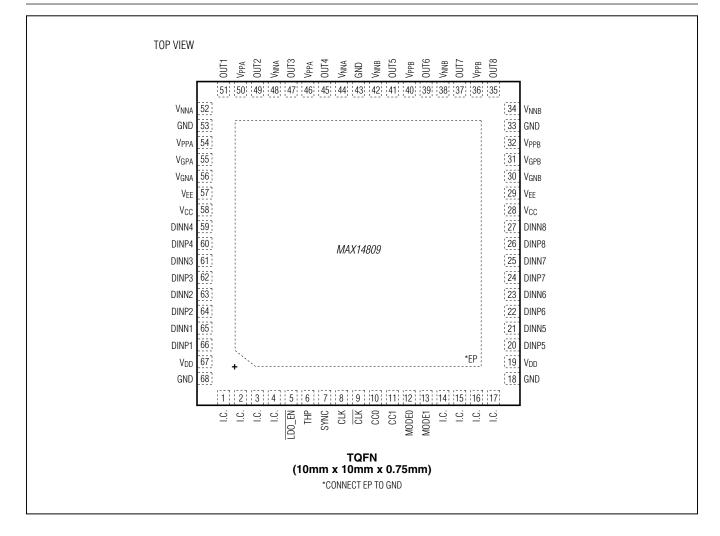
20/div

 $(V_{DD} = +5V, V_{CC} = +5V, V_{EE} = -5V, V_{PP} = +100V, V_{NN} = -100V, R_L = 1k\Omega, C_L = 240pF$ , unless otherwise noted. Typical values are at  $T_A = +25^{\circ}C$ .)



**Pin Configurations** 





**Pin Configurations (continued)** 

# Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch

## **Pin Description**

PIN					
	MAX14808 MAX14809 NAM		FUNCTION		
1	_	LVOUT1	Low-Voltage T/R Switch Output 1		
2	_	LVOUT2	Low-Voltage T/R Switch Output 2		
3		LVOUT3	Low-Voltage T/R Switch Output 3		
4	_	LVOUT4	Low-Voltage T/R Switch Output 4		
	1–4, 14–17	I.C.	Internally Connected. Connect I.C. to GND externally.		
5	5	LDO_EN	Internal Supply Generator Control Input. Drive $\overline{\text{LDO}_{EN}}$ high to disable the internal power supply when using an external power supply on V <sub>GPA</sub> , V <sub>GPB</sub> , V <sub>GNA</sub> , and V <sub>GNB</sub> . $\overline{\text{LDO}_{EN}}$ has an internal 10k $\Omega$ pulldown resistor to GND.		
6	6	THP	Open-Drain Thermal-Protection Output. THP asserts and sinks a 3mA current to GND when the junction temperature exceeds +150°C.		
7	7	SYNC	CMOS Control Input. Drive SYNC high to enable clocked-input mode. Drive SYNC low to operate in transparent mode (see the <i>Truth Tables</i> section).		
8	8	CLK	CMOS Control Input. Clock positive phase input. Data inputs are clocked in at the rising edge of CLK and CLK in differential clocked mode or at the rising edge of CLK in single-ended clocked mode. Clock maximum frequency is 160MHz.		
9	9	CLK	CMOS Control Input. Clock negative phase input. Data inputs are clocked in at the edge of CLK and CLK in differential clocked mode. Clock maximum frequency is 160MHz. If CLK is connected to GND, the CLK input is a single-ended logic-level clock input. Otherwise, CLK and CLK are self-biased differential clock inputs.		
10	10	CC0	Current Control Input. Control current capability (see the Truth Tables section).		
11	11	CC1	Current Control Input. Control current capability (see the Truth Tables section).		
12	12	MODE0	Mode Control Input. Control operation mode (see the Truth Tables section).		
13	13	MODE1	Mode Control Input. Control operation mode (see the Truth Tables section).		
14		LVOUT5	Low-Voltage T/R Switch Output 5		
15	_	LVOUT6	Low-Voltage T/R Switch Output 6		
16		LVOUT7	Low-Voltage T/R Switch Output 7		
17		LVOUT8	Low-Voltage T/R Switch Output 8		
18, 33, 43, 53, 68	18, 33, 43, 53, 68	GND	Ground		
19, 67	19, 67	V <sub>DD</sub>	Logic Supply Voltage. Bypass $V_{DD}$ (both pins) to GND with a 0.1µF capacitor as close as possible to the device.		
20	20	DINP5	Digital Signal Positive Input 5 (see the <i>Truth Tables</i> section)		
21	21	DINN5	Digital Signal Negative Input 5 (see the <i>Truth Tables</i> section)		
22	22	DINP6	Digital Signal Positive Input 6 (see the <i>Truth Tables</i> section)		
23	23	DINN6	Digital Signal Negative Input 6 (see the <i>Truth Tables</i> section)		
24	24	DINP7	Digital Signal Positive Input 7 (see the <i>Truth Tables</i> section)		
25	25	DINN7	Digital Signal Negative Input 7 (see the <i>Truth Tables</i> section)		
26	26	DINP8	Digital Signal Positive Input 8 (see the <i>Truth Tables</i> section)		
27	27	DINN8	Digital Signal Negative Input 8 (see the Truth Tables section)		

# Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch

PIN			FUNCTION		
MAX14808	MAX14809	NAME	FUNCTION		
28, 58	28, 58	V <sub>CC</sub>	$V_{CC}$ Supply Voltage. Bypass $V_{CC}$ (both pins) to GND with a 0.1 $\mu F$ capacitor as close as possible to the device.		
29, 57	29, 57	$V_{EE}$	$V_{\mbox{\scriptsize EE}}$ Supply Voltage. Bypass $V_{\mbox{\scriptsize EE}}$ (both pins) to GND with a 0.1 $\mu\mbox{\scriptsize F}$ capacitor as close as possible to the device.		
30	30	V <sub>GNB</sub>	Driver Voltage Supply Output. Connect a $1\mu\text{F}$ capacitor to $V_{\text{NNB}}$ as close as possible to the device.		
31	31	V <sub>GPB</sub>	Driver Voltage Supply Output. Connect a $1\mu\text{F}$ capacitor to $V_{\text{PPB}}$ as close as possible to the device.		
32, 36, 40	32, 36, 40	V <sub>PPB</sub>	High-Voltage Positive Supply Input. Bypass $V_{\mbox{PPB}}$ to GND with a 0.1 $\mu\mbox{F}$ capacitor as close as possible to the device.		
34, 38, 42	34, 38, 42	V <sub>NNB</sub>	High-Voltage Negative Supply Input. Bypass $V_{\mbox{NNB}}$ to GND with a 0.1 $\mu\mbox{F}$ capacitor as close as possible to the device.		
35	35	OUT8	Pulser Output 8		
37	37	OUT7	Pulser Output 7		
39	39	OUT6	Pulser Output 6		
41	41	OUT5	Pulser Output 5		
44, 48, 52	44, 48, 52	V <sub>NNA</sub>	High-Voltage Negative Supply Input. Bypass $V_{\mbox{NNA}}$ to GND with a $0.1\mu\mbox{F}$ capacitor as close as possible to the device.		
45	45	OUT4	Pulser Output 4		
46, 50, 54	46, 50, 54	V <sub>PPA</sub>	High-Voltage Positive Supply Input. Bypass $V_{PPA}$ to GND with a 0.1µF capacitor as close as possible to the device.		
47	47	OUT3	Pulser Output 3		
49	49	OUT2	Pulser Output 2		
51	51	OUT1	Pulser Output 1		
55	55	V <sub>GPA</sub>	Driver Voltage Supply Output. Connect a $1\mu F$ capacitor to $V_{\mbox{PPA}}$ as close as possible to the device.		
56	56	V <sub>GNA</sub>	Driver Voltage Supply Output. Connect a $1\mu F$ capacitor to $V_{\mbox{NNA}}$ as close as possible to the device.		
59	59	DINN4	Digital Signal Negative Input 4 (see the Truth Tables section)		
60	60	DINP4	Digital Signal Positive Input 4 (see the Truth Tables section)		
61	61	DINN3	Digital Signal Negative Input 3 (see the Truth Tables section)		
62	62	DINP3	Digital Signal Positive Input 3 (see the <i>Truth Tables</i> section)		
63	63	DINN2	Digital Signal Negative Input 2 (see the Truth Tables section)		
64	64	DINP2	Digital Signal Positive Input 2 (see the <i>Truth Tables</i> section)		
65	65	DINN1	Digital Signal Negative Input 1 (see the Truth Tables section)		
66	66	DINP1	Digital Signal Positive Input 1 (see the Truth Tables section)		
		EP	Exposed Pad. Connect EP to GND. Not intended as an electrical connection point.		

**Pin Description (continued)** 

### **Detailed Description**

The MAX14808/MAX14809 octal three-level/quad fivelevel, high-voltage (HV) pulser devices generate highfrequency, HV bipolar pulses (up to  $\pm 105$ V) from lowvoltage control logic inputs for driving piezoelectric transducers in ultrasound systems. All 8 channels have embedded overvoltage-protection diodes and integrated active return-to-zero clamp. Both devices have embedded independent (floating) power supplies (FPSs) and level shifters that allow signal transmission without the need for external HV capacitors. The MAX14808 also features eight integrated transmit receive (T/R) switches. The MAX14809 does not have the T/R switch function.

The devices feature two modes of operation, an octal three-level pulser mode (with integrated active return-to-zero clamp) or a quad five-level pulser mode. In octal three-level pulser mode, each channel is controlled by two logic inputs (DINN\_/DINP\_) and the active return to zero features half the current driving of the pulser, 1A (typ). In quad five-level pulser mode, each channel is controlled by three logic inputs and the active return to zero has the same current driving of the pulser, 2A (typ).

The devices can operate both in clocked and transparent mode. In clocked mode, data inputs can be synchronized with a clean differential or single-ended clock to reduce phase noise associated with FPGA output signals that are detrimental for Doppler analysis. In transparent mode, the synchronization feature is disabled and output reflects the data input after an 18ns delay. Both devices feature adjustable maximum current (0.5A to 2A) to reduce power consumption when full current capability is not required.

The devices feature integrated grass-clipping diodes (with low parasitic capacitance) for receive (Rx) and

transmit (Tx) isolations. Both devices feature a damping circuit that can be activated as soon as the transmit burst is over. The damping circuit has a typical on-resistance of 500 $\Omega$ . It fully discharges the pulser's output internal node before the grass-clipping diodes.

### **Operation Mode**

The devices have four operation modes: shutdown, octal three-level, quad five-level dual, and transmit disable. Use the MODE0 and MODE1 inputs to select the operation mode.

#### **Shutdown Mode**

All channels are disabled, no transmission and reception is possible. This mode has the lowest power consumption. See Table 1.

#### **Octal Three-Level Mode**

The devices operate in eight independent channels. Each channel can generate a three-level pulse. The high-side and low-side FET of each channel are capable of providing 2.0A current, while the clamp is capable of 1A current. See Table 2.

#### **Quad Five-Level Dual Mode**

The devices operate in four independent channels. Each channel can generate a five-level pulse. The devices feature independent dual-voltage supplies (V<sub>NNA</sub>, V<sub>NNB</sub>, V<sub>PPA</sub>, and V<sub>PPB</sub>) and can generate pulses among GND, V<sub>PPA</sub>, and V<sub>NNA</sub> or among GND, V<sub>PPB</sub>, and V<sub>NNB</sub>. The high-side and low-side FET as well as the clamp of each channel can provide 2.0A current. See <u>Table 3</u>.

#### **Transmit Disable Mode**

All eight high-voltage transmit channels are disabled, no pulse transmission is possible. The T/R switch (MAX14808 only) can be turn-on (to receive low-voltage signals) or turn-off (for isolation). See Table 4.

## **Truth Tables**

### Table 1. Shutdown Mode (MODE0 = Low, MODE1 = Low)

INP	UTS	OUTPUTS		
DINN_	DINP_	OUT_ LVOUT_ (MAX14808 ONLY)		
Х	Х	High impedance	High impedance (T/R switch off)	

X = Don't care

### **Truth Tables (continued)**

### Table 2. Octal Three-Level Mode (MODE0 = High, MODE1 = Low, V<sub>NNA</sub> = V<sub>NNB</sub>, V<sub>PPA</sub> = V<sub>PPB</sub>)

IN	PUTS	OUTPUTS		
DINN_	DINP_	OUT_	LVOUT_ (MAX14808 ONLY)	
0	0	Clamp on (damp off)	T/R switch off (LVOUT_ = GND)	
1	0	V <sub>NNA</sub> /V <sub>NNB</sub> (damp off)	T/R switch off (LVOUT_ = GND)	
0	1	V <sub>PPA</sub> /V <sub>PPB</sub> (damp off)	T/R switch off (LVOUT_ = GND)	
1	1	Clamp on (damp on)	T/R switch on	

0 = logic-low, 1 = logic-high

### Table 3. Quad Five-Level Dual Mode (MODE0 = Low, MODE1 = High)

	INPUTS				OUTPUTS			
DINNx x = 1, 2, 3, 4	DINPx x = 1, 2, 3, 4	DINNy y = 5, 6, 7, 8	DINPy y = 5, 6, 7, 8	OUTx = OUTy	LVOUTy y = 1, 2, 3, 4 (MAX14808 ONLY)	LVOUTy y = 5, 6, 7, 8 (MAX14808 ONLY)		
0	0	х	0	High impedance (damp off)	T/R switch off (LVOUT_ = GND)	T/R switch off (LVOUT_ = GND)		
0	0	х	1	Clamp on (damp off)	T/R switch off (LVOUT_ = GND)	T/R switch off (LVOUT_ = GND)		
0	1	0	х	V <sub>PPB</sub> (damp off)	T/R switch off (LVOUT_ = GND)	T/R switch off (LVOUT_ = GND)		
1	0	0	х	V <sub>NNB</sub> (damp off)	T/R switch off (LVOUT_ = GND)	T/R switch off (LVOUT_ = GND)		
0	1	1	х	V <sub>PPA</sub> (damp off)	T/R switch off (LVOUT_ = GND)	T/R switch off (LVOUT_ = GND)		
1	0	1	х	V <sub>NNA</sub> (damp off)	T/R switch off (LVOUT_ = GND)	T/R switch off (LVOUT_ = GND)		
1	1	1	Х	Clamp on (damp on)	T/R switch on	T/R switch off		

**Note:** Only three control inputs (DINNx, DINPx, DINNy) are required for five-level, dual-mode operation. DINPy can be connected to GND or VDD.

X = Don't care, 0 = logic-low, 1 = logic-high

### Table 4. Transmit Disable Mode (MODE0 = High, MODE1 = High)

INP	UTS	OUTPUTS	
DINN_	DINP_	OUT_	LVOUT_ (MAX14808 ONLY)
0	0	High impedance (damp off)	T/R switch off (LVOUT_ = GND)
1	0	High impedance (damp off)	T/R switch off (LVOUT_ = GND)
0	1	High impedance (damp off)	T/R switch off (LVOUT_ = GND)
1	1	High impedance (damp on)	T/R switch on

0 = logic-low, 1 = logic-high

## Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch

#### **Current Capability Selection**

The devices feature pulser current drive capability selection. Two control inputs (CC0, CC1) control the current drive capability (Table 5).

#### Sync Function

The devices provide the ability to resynchronize all the data inputs by means of a clean clock signal. In ultrasound systems, the FPGA output signals are often affected by a high jitter. The jitter induces phase noise that is detrimental in Doppler analysis. The input clock

### **Table 5. Current Drive Selection**

INP	UTS	PULSER OUTPUT
CC0	CC1	CURRENT (typ)
0	0	2A
1	0	1.5A
0	1	1A
1	1	0.5A

can be either a differential signal or a single-ended signal running up to 160MHz. Data are clocked in on the rising edge of the CLK input (falling edge of  $\overline{\text{CLK}}$ ). Connect  $\overline{\text{CLK}}$  to GND for single-ended operation. The sync feature can be enabled or disabled by the SYNC control input. Drive the SYNC input low to disable the synchronization function (no external clock signal). Drive the SYNC input high to enable the synchronization function (with an external clock signal). Figure 6 shows the simplified CLK and  $\overline{\text{CLK}}$  inputs schematic.

#### T/R Switches (MAX14808 Only)

Each channel features a low-power T/R switch. The T/R switch recovery time after the transmission is less than 1.2µs. The T/R switches are controlled by the same pulser digital inputs (see the <u>Truth Tables</u> section). No dedicated input signals are required to activate/deactivate the T/R switches. The integrated T/R switches do not require any special timings and can operate synchronously with the digital pulser. To minimize the leakage current during transmission, it's recommended to switch off the T/R switches 3µs before the beginning of the transmit burst.

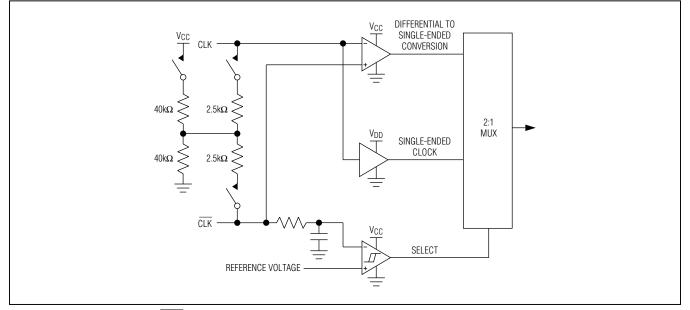


Figure 6. Simplified CLK and CLK Inputs Schematic

## Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch

#### **Grass-Clipping Diodes**

A pair of diodes in antiparallel configuration (referred to as grass-clipping diodes) is presented at each pulser's output. The diodes' reverse capacitance is extremely low, allowing a perfect isolation between the receive path and the actual pulser's output stage.

#### Active Damp Circuit

An active damp circuit is integrated between the internal pulser output node (before grass-clipping diodes) and GND. The purpose of this circuit is to fully discharge the pulser output internal node so that the node is not left in high-impedance condition as soon as the transmit burst is over. This results in two main advantages:

- 1) The grass-clipping isolation is more effective.
- Suppression of any low-frequency oscillation of a node that could be detrimental for Doppler mode performances.

#### Independent (<u>Floating</u>) Power-Supply Enable (LDO\_EN)

The devices feature the LDO\_EN control input to enable/ disable the internal FPSs. This allows the usage of external high-efficiency power supplies to save system power. This option must be considered only for special applications requiring extremely low power dissipation. The low power dissipation of the embedded FPSs already meets power requirements in most of the cases. Drive LDO\_EN low or leave unconnected to enable the internal FPSs; drive LDO\_EN high to disable the internal FPSs.

#### **Thermal Warning Outputs**

The devices feature an open-drain thermal-protection output (THP). When the internal junction temperature exceeds +150°C, the devices automatically enter shutdown mode and THP asserts. The devices reenter normal operation and the THP deasserts when the die temperature drops below +130°C.

#### **Power Sequencing**

When using the embedded FPSs ( $\overline{\text{LDO}_{\text{EN}}}$  = low), the devices do not require any power-up/power-down sequence. When external FPSs are used ( $\overline{\text{LDO}_{\text{EN}}}$  = high), the conditions VGP\_ > (VEE - 0.6V) and VGN\_ < (VCC + 0.6V) must be satisfied during the entire power-up/power-down transients (see the electrical characteristics tables).

### **Applications Information**

#### **Exposed Pad and Layout Concerns**

The devices provide an exposed pad (EP) underneath the TQFN package for improved thermal performance. Connect EP to GND externally and do not run traces under the package to avoid possible short circuits. To aid heat dissipation, connect EP to a similarly sized pad on the component side of the PCB. This pad should be connected through to the solder-side copper by several plated holes to a large heat-spreading copper area to conduct heat away from the device.

The devices' high-speed pulser requires low-inductance bypass capacitors to their supply inputs. High-speed PCB trace design practices are recommended. Pay particular attention to minimize trace lengths and use sufficient trace width to reduce inductance. Use of surface-mount components is recommended.

#### **Typical Application Circuit**

Figure 7 shows the MAX14808 in an octal three-level pulsing application.

## Octal Three-Level/Quad Five-Level High-Voltage 2A Digital Pulsers with T/R Switch

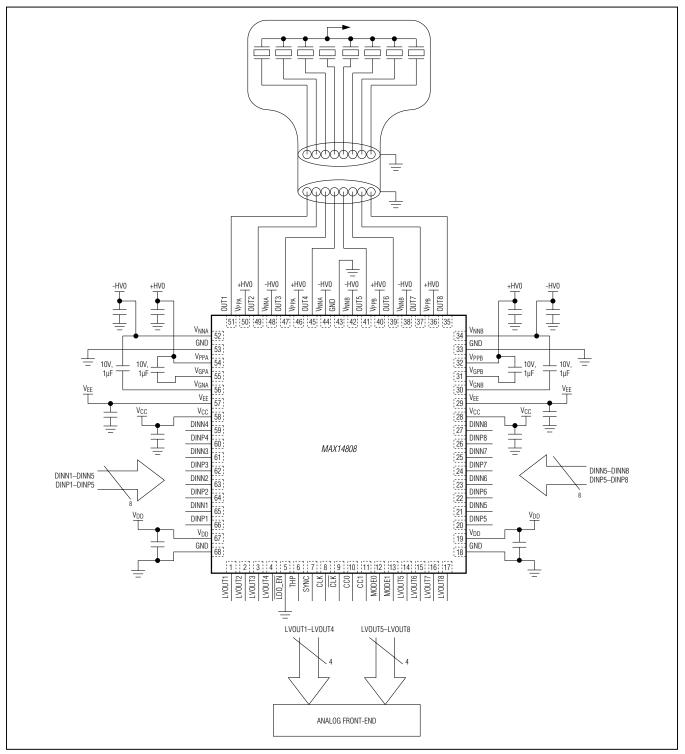
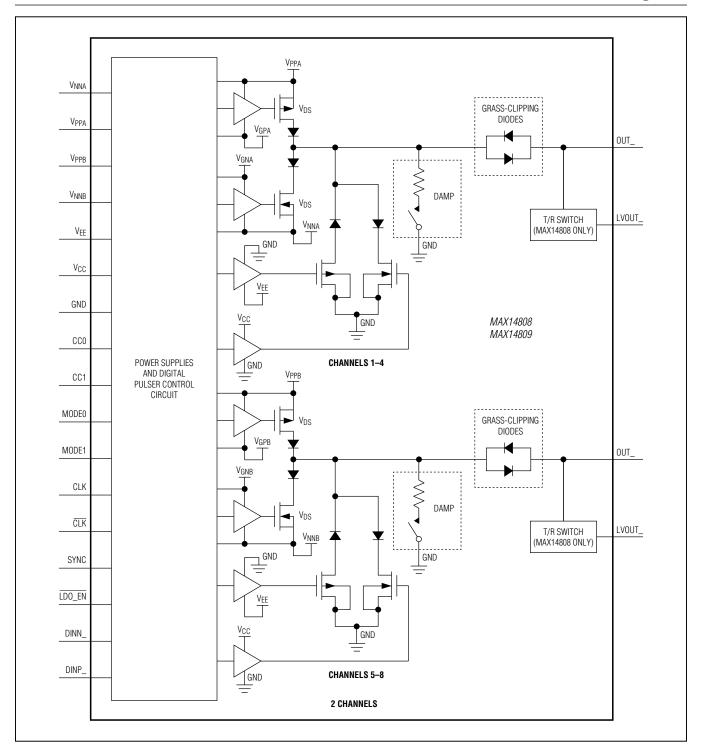


Figure 7. Octal Three-Level Pulsing (MAX14808)

**Functional Diagram** 



### **Ordering Information**

PART	TRANSMIT CHANNELS	T/R SWITCHES	TEMP RANGE	PIN-PACKAGE
MAX14808ETK+	Yes	Yes	-40°C to +85°C	68 TQFN-EP*
MAX14809ETK+	Yes	No	-40°C to +85°C	68 TQFN-EP*

+Denotes a lead(Pb)-free/RoHS-compliant package. \*EP = Exposed pad.

### **Chip Information**

PROCESS: BiCMOS

## **Package Information**

For the latest package outline information and land patterns (footprints), go to <u>www.maximintegrated.com/packages</u>. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE	PACKAGE	OUTLINE	LAND
TYPE	CODE	NO.	PATTERN NO.
68 TQFN-EP	T6800+4	<u>21-0142</u>	<u>90-0101</u>

## **Revision History**

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REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	9/12	Initial release	—
1	3/13	Updated the <i>DC Electrical Characteristics</i> and <i>AC Electrical Characteristics</i> tables; updated TOC 9 in the <i>Typical Operating Characteristics</i> section; removed the future product notation from the MAX14809 in the <i>Ordering Information</i> table	5–8, 11, 17, 30
2	1/14	Updated the DC Electrical Characteristics and AC Electrical Characteristics tables	8, 9, 11



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